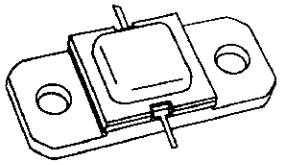
SGS-THOMSON MICROELECTRONICS

MSC81250M

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

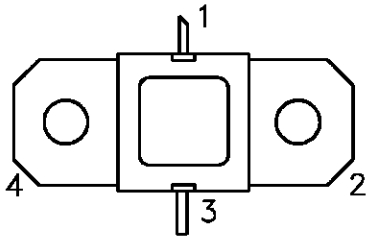
- REFRACTORY\GOLD METALLIZATION
- RUGGEDIZED VSWR 20:1
- INTERNAL INPUT/OUTPUT MATCHING
- LOW THERMAL RESISTANCE
- METAL/CERAMIC HERMETIC PACKAGE
- P_{OUT} = 250 W MIN. WITH 6.2 dB GAIN



.400 x .400 2NLFL (S042)
hermetically sealed

ORDER CODE	BRANDING
MSC81250M	81250M

PIN CONNECTION



1. Collector
2. Base
3. Emitter
4. Base

DESCRIPTION

The MSC81250M device is a high power pulsed transistor specifically designed for DME/TACAN avionics applications.

This device is capable of withstanding a minimum 20:1 load VSWR at any phase angle under full rated conditions. Low RF thermal resistance and semi automatic wire bonding techniques ensure high reliability and product consistency.

The MSC81250M is housed in the unique AMPAC™ package with internal input/output matching structures.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation* ($T_C \leq 80°C$)	600	W
I_C	Device Current*	17.8	A
V_{CC}	Collector-Supply Voltage*	55	V
T_J	Junction Temperature (Pulsed RF Operation)	250	°C
T_{STG}	Storage Temperature	– 65 to +200	°C

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	0.20	°C/W

*Applies only to rated RF amplifier operation

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	I_C = 10mA	I_E = 0mA	65	—	—	V
BV_{EBO}	I_E = 1mA	I_C = 0mA	3.5	—	—	V
BV_{CER}	IC = 25mA	R_{BE} = 10Ω	65	—	—	V
I_{CES}	V_{CE} = 50V		—	—	25	mA
h_{FE}	V_{CE} = 5V	I_C = 1A	15	—	120	—

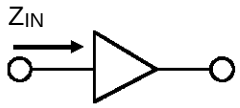
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	f = 1025 — 1150 MHz	P_{IN} = 60 W	V_{CC} = 50 V	250	270	—	W
η_c	f = 1025 — 1150 MHz	P_{IN} = 60 W	V_{CC} = 50 V	40	38	—	%
G_P	f = 1025 — 1150 MHz	P_{IN} = 60 W	V_{CC} = 50 V	6.2	6.5	—	dB

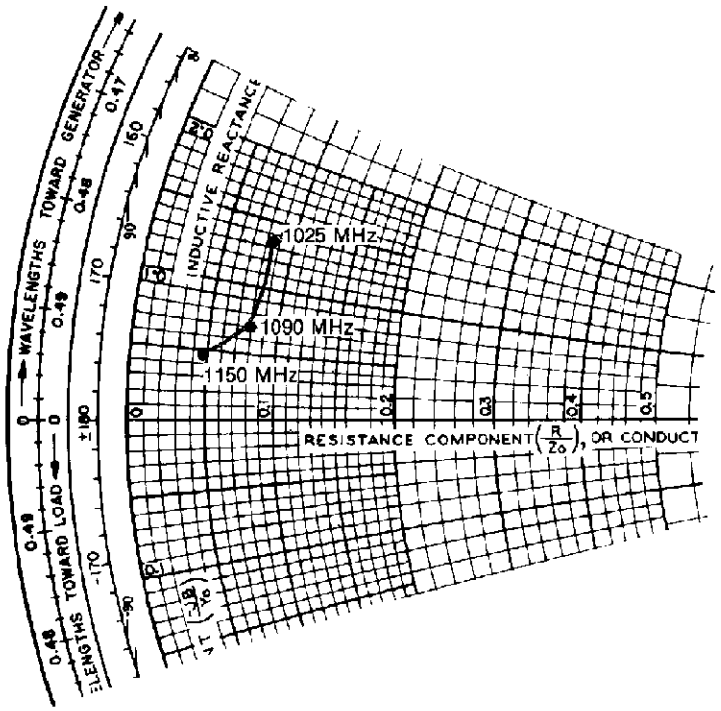
Note: Pulse Width = 10μSec
Duty Cycle = 1%

IMPEDANCE DATA

TYPICAL INPUT IMPEDANCE

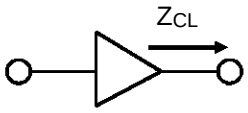


P_{IN} = 60 W
V_{CC} = 50 V
Normalized to 50 ohms

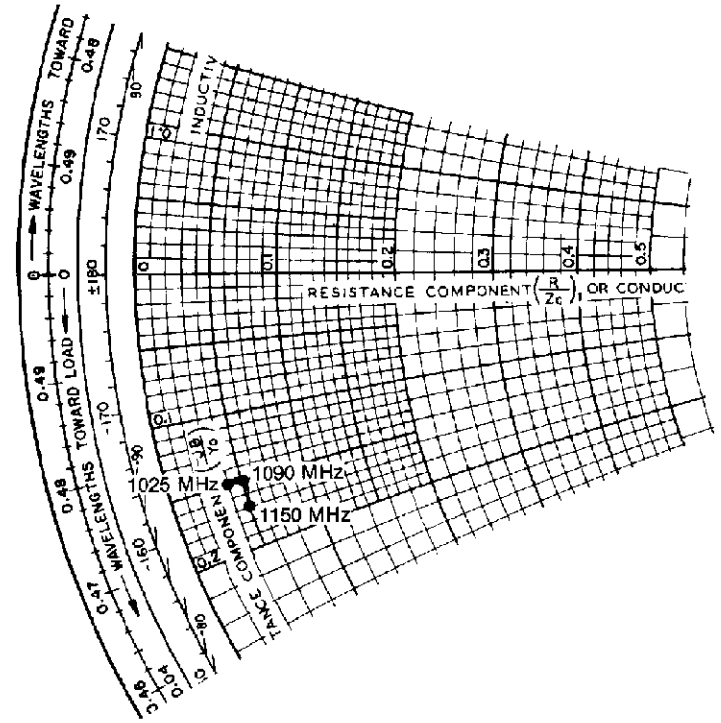


FREQ.	Z_{IN} (Ω)	Z_{CL} (Ω)
L = 1025 MHz	4.2 + j 6.7	2.0 – j 7.5
M = 1090 MHz	4.0 + j 3.5	2.5 – j 7.5
H = 1150 MHz	2.3 + j 2.3	2.5 – j 8.5

TYPICAL COLLECTOR LOAD IMPEDANCE

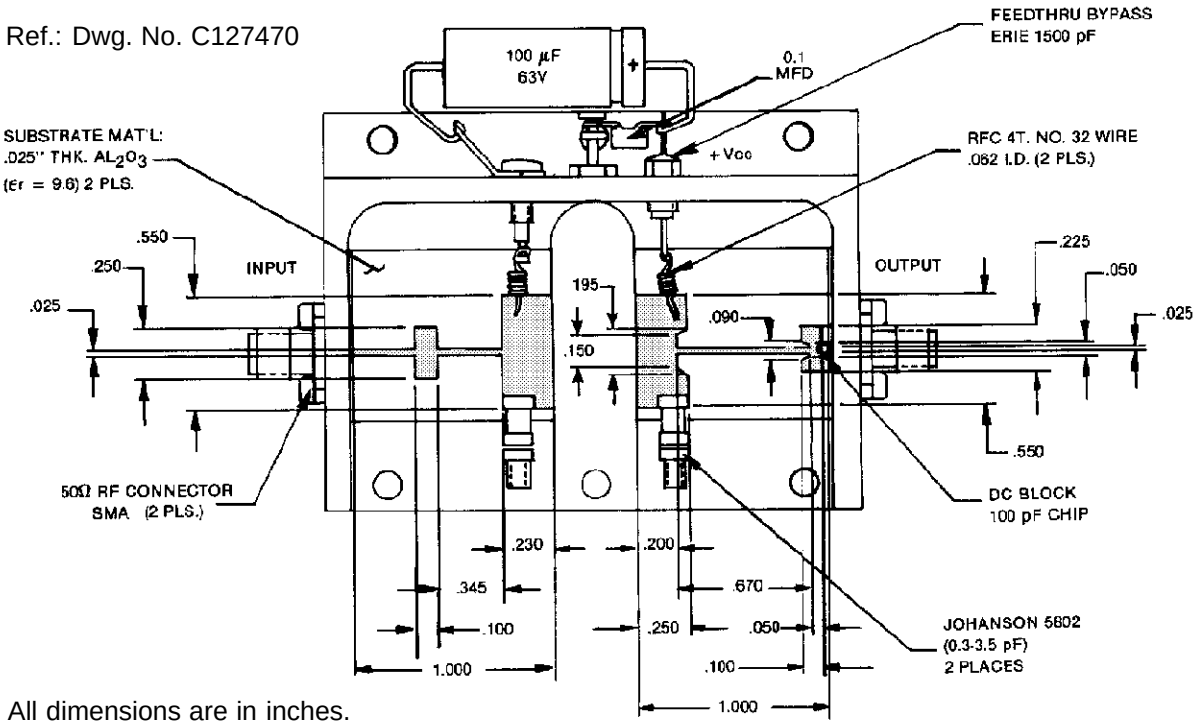


P_{IN} = 60 W
V_{CC} = 50 V
Normalized to 50 ohms



TEST CIRCUIT

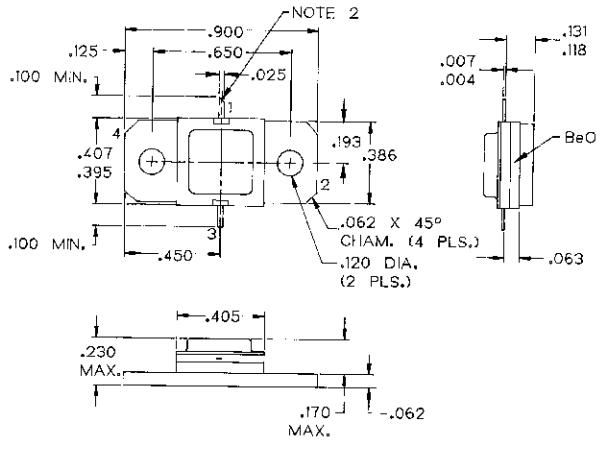
Ref.: Dwg. No. C127470



All dimensions are in inches.

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.: J113214F



NOTES:
1. ALL TOLERANCE ± .010 EXCEPT WHERE NOTED; DIMENSIONS IN INCHES.
2. COLLECTOR LEAD SLANT CUT.